

June 1999

USB10P

P-Channel 2.5V Specified PowerTrench™ MOSFET

General Description

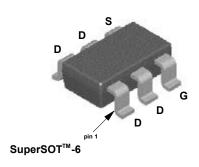
This P-Channel 2.5V specified MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

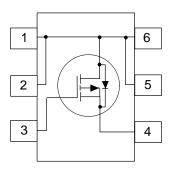
These devices are well suited for battery power applications: load switching and power management, battery charging circuits, and DC/DC conversion.

Features

- -4.5 A, -20 V. $R_{DS(ON)} = 0.045~\Omega~$ @ $V_{GS} =$ -4.5 V $R_{DS(ON)} = 0.065~\Omega~$ @ $V_{GS} =$ -2.5 V.
- Low gate charge (13nC typical).
- High performance trench technology for extremely low R_{DE/OND}.
- SuperSOTTM-6 package: small footprint (72% smaller than standard SO-8); low profile (1mm thick).







Absolute Maximum Ratings

T_A = 25°C unless otherwise note

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		-20	V
V _{GSS}	Gate-Source Voltage - Continuous		±8	V
I _D	Drain Current - Continuous	(Note 1a)	-4.5	А
	- Pulsed		-20	
P _D	Maximum Power Dissipation	(Note 1a)	1.6	W
		(Note 1b)	0.8	
T_J , T_{STG}	Operating and Storage Temperatur	e Range	-55 to 150	°C
THERMA	L CHARACTERISTICS			
R _{eJA}	Thermal Resistance, Junction-to-A	mbient (Note 1a)	78	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-C	ase (Note 1)	30	°C/W

Symbol	Parameter	Min	Тур	Max	Units	
OFF CHAR	ACTERISTICS					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-20			V
$\Delta BV_{DSS}/\Delta T_{J}$	Breakdown Voltage Temp. Coefficient	I _D =-250 μA, Referenced to 25 °C		-18		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V}, \ V_{GS} = 0 \text{ V}$			-1	μA
		T _J = 55 °C			-10	μA
I _{GSSF}	Gate - Body Leakage, Forward	$V_{GS} = 8 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate - Body Leakage, Reverse	$V_{GS} = -8 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
ON CHARA	CTERISTICS (Note 2)	•		_		
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-0.4	-0.9	-1.5	V
$\Delta V_{GS(th)}/\Delta T_{J}$	Gate Threshold VoltageTemp.Coefficient	I _D =-250 μA, Referenced to 25 °C		3		mV/°C
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = -4.5 \text{ V}, I_D = -4.5 \text{ A}$		0.039	0.045	Ω
, ,		T _J = 125 °C		0.054	0.072	1
		$V_{GS} = -2.5 \text{ V}, I_{D} = -3.8 \text{ A}$		0.057	0.065	1
I _{D(on)}	On-State Drain Current	$V_{GS} = -4.5 \text{ V}, V_{DS} = -5 \text{ V}$	-20			Α
g _{FS}	Forward Transconductance	$V_{DS} = -10 \text{ V}, I_{D} = -4.5 \text{ A}$		6.5		S
DYNAMIC C	HARACTERISTICS					
C _{iss}	Input Capacitance	$V_{DS} = -10 \text{ V}, \ V_{GS} = 0 \text{ V},$		1240		pF
C _{oss}	Output Capacitance	f = 1.0 MHz		270		pF
C _{rss}	Reverse Transfer Capacitance		100		pF	
SWITCHING	CHARACTERISTICS (Note 2)					
t _{D(on)}	Turn - On Delay Time	$V_{DD} = -5 \text{ V}, \ I_{D} = -1 \text{ A},$		8	16	ns
t _r	Turn - On Rise Time	$V_{GS} = -4.5 \text{ V}, R_{GEN} = 6 \Omega$		15	27	ns
$t_{D(off)}$	Turn - Off Delay Time			45	65	ns
t _f	Turn - Off Fall Time			30	50	ns
Q_g	Total Gate Charge	$V_{DS} = -10 \text{ V}, I_{D} = -4.5 \text{ A},$		13	19	nC
Q_{gs}	Gate-Source Charge	$V_{GS} = -5 V$		1.8		nC
Q_{gd}	Gate-Drain Charge			3		nC
DRAIN-SOU	RCE DIODE CHARACTERISTICS					
I _s	Continuous Source Diode Current				-1.3	Α
$\overline{V_{SD}}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = -1.3 \text{ A}$ (Note 2)		-0.75	-1.2	V

Notes:

^{1.} R_{guA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{guC} is guaranteed by design while R_{guC} is determined by the user's board design.

a. 78°C/W when mounted on a 1 in 2 pad of 2oz Cu on FR-4 board.

b. 156°C/W when mounted on a minimum pad.

^{2.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

Typical Electrical Characteristics

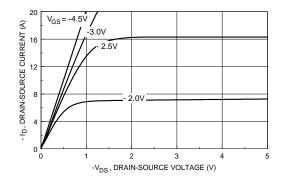


Figure 1. On-Region Characteristics.

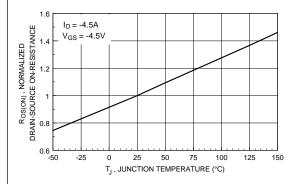


Figure 3. On-Resistance Variation with Temperature.

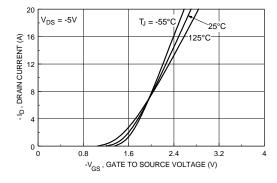


Figure 5.Transfer Characteristics.

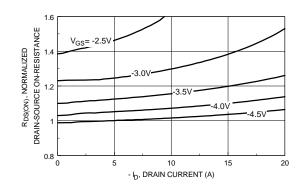


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

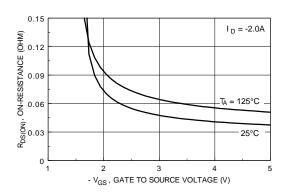


Figure 4. On Resistance Variation with Gate-to-Source Voltage.

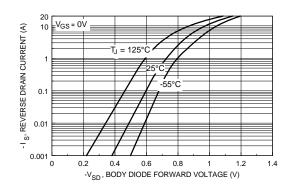


Figure 6. Body Diode Forward Voltage
Variation with Source Current
and Temperature.

Typical Electrical Characteristics

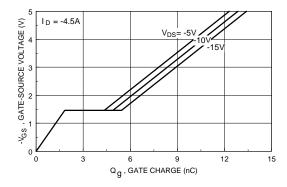


Figure 7. Gate Charge Characteristics.

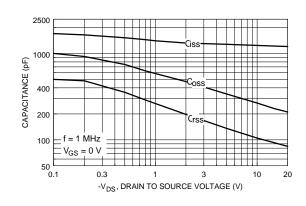
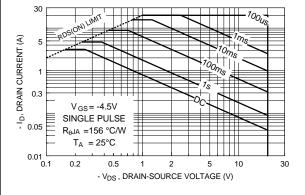


Figure 8. Capacitance Characteristics.



SINGLE PULSE
R₀JA =156°C/W
T_A = 25°C

0.01
0.1
1
10
100
300
SINGLE PULSE
TIME (SEC)

Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

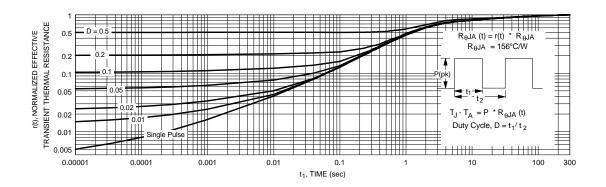
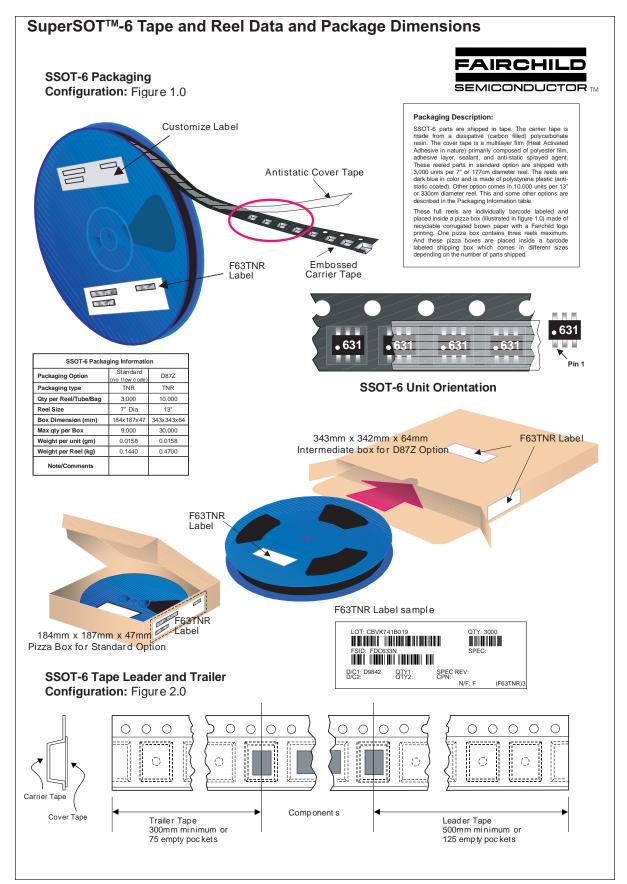


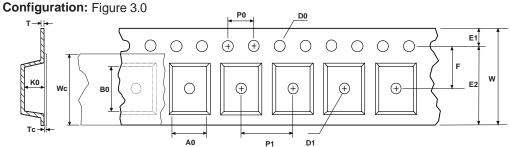
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.





SSOT-6 Embossed Carrier Tape



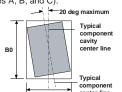


Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SSOT-6 (8mm)	3.23 +/-0.10	3.18 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.37 +/-0.10	0.255 +/-0.150	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

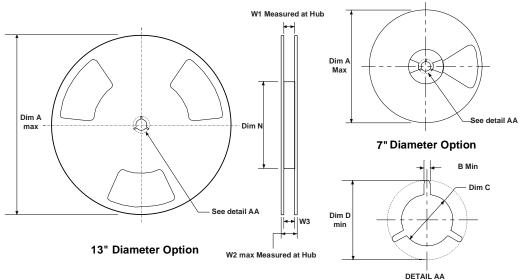


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

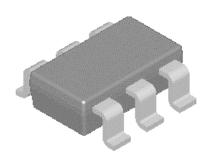
SSOT-6 Reel Configuration: Figure 4.0

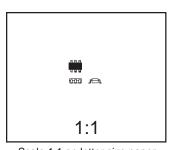


Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

SuperSOT™-6 Tape and Reel Data and Package Dimensions, continued

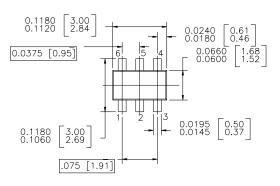
SuperSOT -6 (FS PKG Code 31, 33)

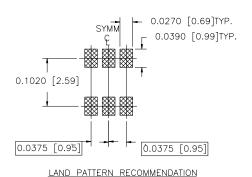




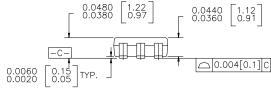
Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

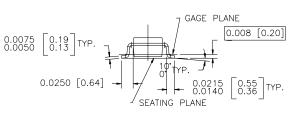
Part Weight per unit (gram): 0.0158





CONTROLLING DIMENSION IS INCH VALUES IN [] ARE MILLIMETERS





NOTES: UNLESS OTHERWISE SPECIFIED

1.0 STANDARD LEAD FINISH: 150 MICROINCHES 93.81 MICROMETERS) MINIMUM TIN / LEAD (SOLDER) ON COPPER.

 $2.0\ \mathsf{NO}\ \mathsf{JEDEC}\ \mathsf{REGISTRATION}\ \mathsf{AS}\ \mathsf{OF}\ \mathsf{JULY}\ 1996$

SUPER SOT 6 LEADS

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